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Claims 42-69 are pending. Claims 42, 45, 56, and 59 are rejected and amended.

Reconsideration and reexamination of this application is respectfully requested.

The Examiner rejected claims 45 and 59 under 35 U.S.C. §112, first paragraph, as containing subject matter which was not described in the specification in such a way as to enable one skilled in the art to which it pertains, or with which it is most nearly connected, to make and/or use the invention. Applicants have amended claims 45 and 59 to remove any perceived indefiniteness. Applicants respectfully submit that all of the claims comply with 35 U.S.C. 112.

The Examiner rejected claims 42-52, 54-66, 68 and 69 under 35 U.S.C. §102 (e) as being anticipated by Shimada et al. (US Patent No. 5,852,485). Applicants respectfully traverse the rejection.

Claims 42 and 56 are allowable at least for the reason that claims 42 and 56 recite a combination of elements including a transparent first metal layer and a transparent second metal layer on the gate insulator. None of the cited references teaches or suggests each and every element of the claims.

Shimada et al. discloses the picture element electrode 12 and the counter electrode 11 on the interlayer insulation layer 19 at column 12, lines 44-63.. However, the present invention discloses that the transparent first metal layer and the transparent second metal layer are formed on the gate insulator. Applicants respectfully request that the rejection under 35 U.S.C. 102(e) be withdrawn.

The Examiner rejected claims 53 and 67 under 35 U.S.C. 103(a) as being unpatentable over Shimada et al. (US Patent No. 5,852,485) in view of Ohta et al. (US Patent No. 5,929,958). Applicants respectfully traverse this rejection.

As discussed above Shimada et al. fail to teach or suggest a transparent first metal layer and the transparent second metal layer are formed on the gate insulator. Ohta et al. fail

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to cure the deficiencies of <u>Shimada et al</u>. Applicants respectfully request that the rejection under 35 U.S.C. 103(a) be withdrawn.

Applicants believe the foregoing amendments place the application in condition for allowance and early, favorable action is respectfully solicited. Should the Examiner deem that a telephone conference would further the prosecution of this application, the Examiner is invited to call the undersigned attorney at (202) 496-7371.

If these papers are not considered timely filed by the Patent and Trademark Office, then a petition is hereby made under 37 C.F.R. §1.136. Please credit any overpayment to deposit Account No. 50-0911.

Respectfully submitted,

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## MARKED UP VERSION OF AMENDED CLAIMS

42. (Amended) An in-plane switching liquid crystal display device comprising: first and second substrates;

a plurality of gate and data bus lines on the first substrate, the gate lines being crossed with the data bus lines;

a common line parallel to any one of the gate lines and the data bus lines on the first substrate;

[an] a gate insulator on the first substrate; and

a transparent first metal layer and a transparent second metal layer on the gate insulator.

- 45. (Amended) The device of claim 44, wherein the transparent first metal layer is connected to the [source and] drain electrodes.
- 56. (Amended) A method of forming an in-plane switching liquid crystal display device, comprising:

forming first and second substrates;

forming a plurality of gate and data bus lines on the first substrate, the gate lines being crossed with the data bus lines;

forming a common line in parallel to any one of the gate lines and the data bus lines on the first substrate;

forming [an] a gate insulator on the first substrate; and

a transparent first metal layer and a transparent second metal layer on the gate insulator.

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59. (Amended) The method of claim 58, wherein the transparent first metal layer is connected to the [source and] drain electrodes.

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